

AMENDMENT UNDER 37 C.F.R. § 1.111  
U.S. Appln. No. 09/672,776

area of from 30 to 80 m<sup>2</sup>/g, and

31  
cut  
mechanochemically polishing a metal film on said semiconductor substrate with  
said polishing composition.

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B2  
8. (Amended) The method according to claim 6, wherein said insulating layer is  
made of a material selected from the group consisting of oxidized silicon and nitrided  
silicon.

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